

Scheme 1. Process flow for AS-ALD using e-jet printing. Reprinted with permission from *ACS Nano* 2020, 14, 12, 17262–17272. © Copyright 2020 American Chemical Society.

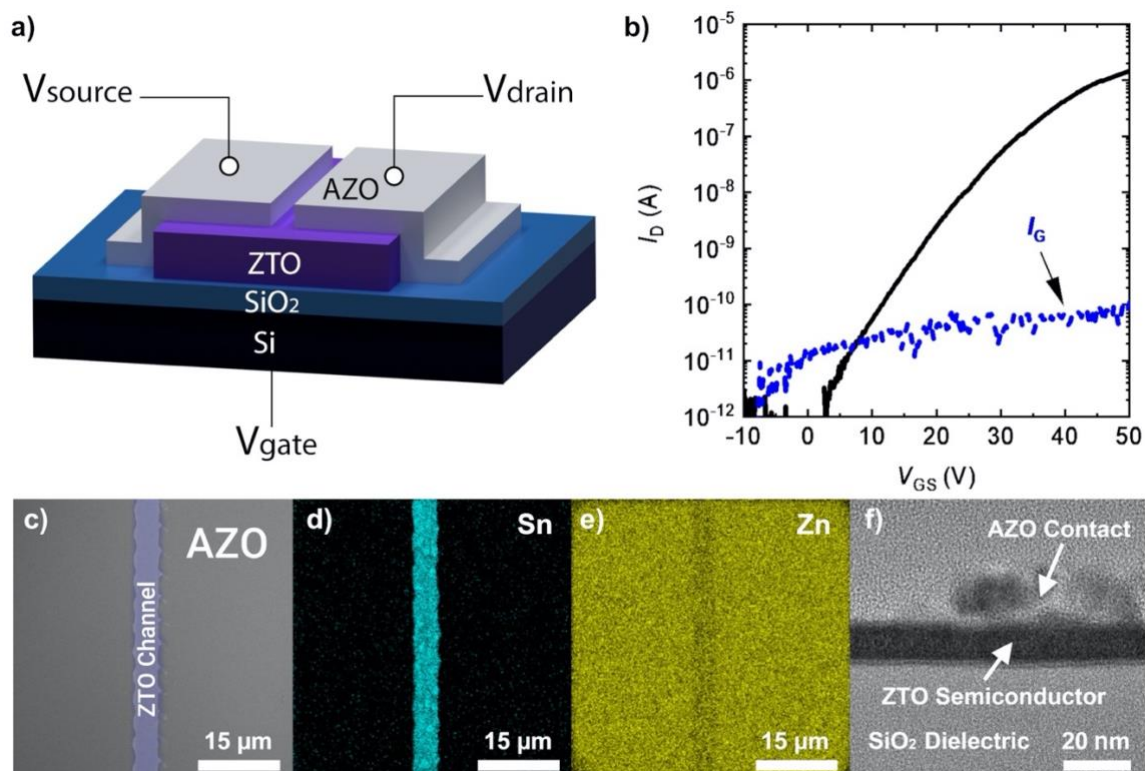
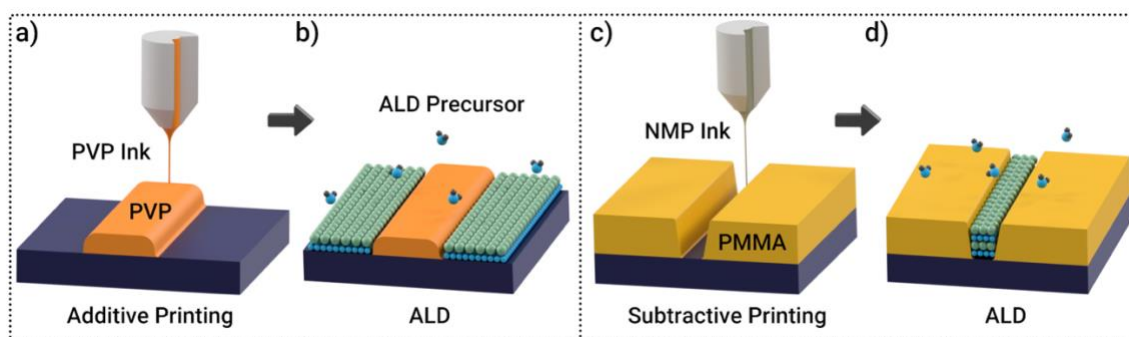


Figure 1. (a) Fabricated TFT structure. (b) Transfer curves of a 5- μm channel length device with $V_{DS} = 1$ V. (c) Top-down SEM image of a device with a 4- μm long channel with corresponding AES mapping of (d) Sn and (e) Zn. (f) Cross-sectional scanning transmission electron microscopy (STEM) image of a 4- μm channel device after selective AZO deposition using additive PVP printing. Reprinted with permission from *ACS Nano* 2020, 14, 12, 17262–17272. Copyright © 2020 American Chemical Society.